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(54) 【発明の名称】 磁気記録媒体用基板の製造方法

(57)【要約】

【課題】 ガラス基板と密着性の高いNiP無電解メッ キ層を有する磁気記録媒体用基板を提供する。

【解決手段】 ガラス基板に、感受性化工程、活性化工 程、NiP無電解メッキ工程を順次設けてなる磁気記録 媒体用基板の製造方法であって、NiP無電解メッキエ 程におけるNiPメッキ浴の温度が60℃以上、かつ7 0℃未満であることを特徴とする磁気記録媒体用基板の 製造方法

【特許請求の範囲】

【請求項1】 ガラス基板に、感受性化工程、活性化工程、NiP無電解メッキ工程を順次設けてなる磁気記録媒体用基板の製造方法であって、NiP無電解メッキ工程におけるNiPメッキ浴の温度が60℃以上、かつ70℃未満であることを特徴とする磁気記録媒体用基板の製造方法

【請求項2】 NiPメッキ浴の温度が、65~69℃ であることを特徴とする請求項1記載の磁気記録媒体用 基板の製造方法

【請求項3】 ガラス基板が、 SiO_2-Li_2O 系結晶化ガラスからなることを特徴とする請求項1または2記載の磁気記録媒体用基板の製造方法

【発明の詳細な説明】

[0001]

【発明の属する技術分野】本発明は、磁気記録媒体用基板の製造方法に関するものである。具体的には、情報産業等で利用される固定型の薄膜磁気記録ディスク等の高記録密度磁気記録媒体における基板の製造方法に関する。特には、ガラス基板と密着性の高いNiP無電解メッキ層を形成する方法に係わる。

[0002]

【従来の技術】近年、コンピュータなどの情報処理装置の外部記憶装置として固定磁気ディスク装置が多く用いられている。この固定磁気ディスク装置に搭載される磁気ディスクは、一般に、アルミニウム合金からなる非磁性基板の表面に、NiP無電解メッキ層を形成し、所要の平滑化処理、テクスチャリング処理などを施した後、その上に、非磁性金属下地層、磁性層、保護層、潤滑層などを順次形成して作製されている。

【0003】磁気ディスク装置では、記録再生用ヘッド が磁気記録媒体上を一定の浮上量で移動しているが、近 年、磁気記録媒体の面記録密度の急激な増加に伴って、 この浮上量が極めて小さくなっている。また、磁気ディ スク装置の小型化、軽量化も急速に進んでおり、これら に対応するためには、磁気記録媒体の表面の粗さをより 一層小さくすることが必要であり、既に媒体表面粗さは Raで数A程度まで小さくなっている。さらに、可搬型 の固定磁気ディスク装置に対応するために磁気ディスク に要求される耐衝撃性も400G~800Gと高い値と なってきているため、耐衝撃性に対して従来のアルミニ ウム合金からなる基板では対応が難しくなっている。そ こで、耐衝撃性、表面平滑性などの見地から、アルミニ ウム合金基板に代わって、極めて小さな表面粗さを達成 することができ、かつ機械的強度にも優れているガラス 基板が使用され始めている。

【0004】NiP無電解メッキを施したアルミニウム合金基板においては、多くの場合、その表面に研磨により基板円周方向に同心円状のテキスチャリングが施されている。これは、主に記録再生用のヘッドと磁気記録媒

体との間の摩擦特性を良好ならしめ、耐久性を確保することを目的としている。また、近年では磁気ディスク装置作動時のヘッドの浮上量が著しく小さくなっていることに伴い、研磨によるテキスチャリングに代えて、CSSゾーンのみにレーザービームによるテキスチャリング、すなわちレーザービームにより突起を形成することが試みられている。 (特開平8-129749号公報等)

【0005】しかしながら、NiP無電解メッキを施したアルミニウム合金基板とは異なり、ガラス板に直接レーザービームを照射して突起を形成することは、突起形状制御性が悪いため極めて困難である。そこで、レーザーテキスチャー技術をガラス基板に適用するためには、予め基板上にNiP無電解メッキ層を形成する必要がある。

【0006】特開昭61-54018号公報等には、ガラス基板上にNiP無電解メッキ膜を形成する方法が提案されている。ところが、ガラス基板へ無電解メッキ法によりNiP層を密着性良く形成することは技術的に困難である。そこで、ガラス基板とNiP無電解メッキ膜の密着性を改善するために、メッキに用いるガラス基板を面を機械的または化学的に粗面化する方法や、無電解メッキの前処理を行う方法が提案されている。例えば、機械的な粗面化方法としては、 Al_2O_3 等の研磨剤を用いた砥石により表面粗さが中心線平均粗さRaで100Å以上研磨する方法が知られており、化学的な祖面化方法としては、アルカリ脱脂した後、フッ化水素酸等でエッチングする方法が知られている。

【0007】また、無電解メッキの前処理を行う方法としては、特開平7-272263号公報、特開平6-212440号公報等に、ガラス基板を塩化第一スズの溶液で増感後、塩化パラジウム溶液で活性化処理を行い、次いで、該ガラス基板を70℃以上、あるいは80℃以上の高温下でNiP無電解メッキを行う方法が提案されている。

[0008]

【発明が解決しようとする課題】しかしながら、これらの方法では、ガラス基板上に良好な磁気ディスクを得るに充分な密着性と平滑性を有するNiP層を無電解メッキ法で形成することができなかった。本発明は、上述の点に鑑みなされたものであり、その目的は、ガラス基板とNiP無電解メッキ層との密着性に優れ、高い耐衝撃性、表面平滑性を有し、しかも、ヘッドの低浮上高さが安定して得られる磁気記録媒体用基板の製造方法を提供することにある。

[0009]

【課題を解決するための手段】本発明者らは、上記実情に鑑み鋭意検討した結果、NiP無電解メッキ工程におけるNiPメッキ浴の温度を制御することにより、上記の諸要件を満たす優れたNiP層が基板上に形成される

ことを見出し、本発明に達したものである。すなわち、本発明の要旨は、ガラス基板に、感受性化工程、活性化工程、NiP無電解メッキ工程を順次設けてなる磁気記録媒体用基板の製造方法であって、NiP無電解メッキ工程におけるNiPメッキ浴の温度が60℃以上、かつ70℃未満であることを特徴とする磁気記録媒体用基板の製造方法に存する。

【0010】以下、本発明を詳細に説明する。本発明のガラス基板としては、特に限定されないが、例えば、結晶化ガラスやアルミノシリケートガラスなどが好ましく使用される。中でも結晶化ガラスが好適である。ガラス基板は、NiP無電解メッキ層との密着性を確保するため、基板表面に微細な凹部を有するガラス基板を用いることが好適である。より具体的には、凹部の最大幅が、20 μ m以下、更に好ましくは10 μ m以下、特に好ましくは5 μ 以下の微細な凹部が好適に使用される。これは、板表面に微細な凹部を有する場合には、この微細な穴の中にNiP膜が形成されるため、物理的アンカー効果を高め、これによりガラス基板とNiPメッキ層との密着を強固にするものと思われる。

【0011】ガラス基板の表面の微細な凹部は、例えば、結晶化ガラス基板においては、フッ酸、フッ化カリウム、フッ化アンモニウム等のフッ酸系のエッチング剤を使用して、化学エッチング処理を行うことにより、形成することができる。これは、結晶化ガラスを用いると、化学エッチングを基板表面のアモルファス領域を選択的にエッチングできるため、表面の平滑性をある程度、独立に凹部を形成できるため好適である。凹部の大きさは、エッチング液の濃度、処理温度、処理時間などを適宜選択することにより制御することが可能である。また、高硬度アルミノシリケート基板においては、遊離砥粒や研削処理により加工することにより、凹部を形成することができる。

【0012】本発明によれば、ガラス基板に、感受性化工程、活性化工程を行い、続いて特定の条件下でNiP無電解メッキを行うことによって、ガラス基板とNiP無電解メッキ層との密着性に優れた磁気記録媒体用基板を得ることができる。そして、通常は、感受性化工程の前には、脱脂工程が設けられる。また、各工程間には水洗工程が設けられ、洗浄水としては、イオン交換水または超純水が適宜使用される。

【0013】脱脂工程は、ガラス基板の表面を洗浄する工程であり、例えば、超純水、アルカリ洗浄剤、酸洗浄剤、界面活性剤などを使用する方法が挙げられる。感受性化工程および活性化工程は、ガラス基板にNiP無電解メッキを開始させるために必要な触媒活性を与える工程である。すなわち、ガラス表面は触媒活性がないため、無電解メッキを開始するためには、ガラスの表面にAu、Pt、Pd、Ag等の貴金属の触媒核を形成する

ことが必要である。

【0014】上記の各工程は、公知の方法により、次のように実施される。(表面技術Vol. 44 No. 10、1993「ガラスと無電解ニッケルめっきの密着性」、堀田慎一他参照。)

感受性化工程において、まず、Sn、Ti、Pd、Hg等からなる2価の金属イオンを吸着させる。通常、0.05g/1程度の塩化スズ水溶液が好適に使用され、常温で塩化スズ水溶液中に1~3分程度浸漬される。次に、活性化工程として、前記の触媒核となる貴金属を含む含む活性化処理溶液に上記のガラス基板を浸漬し、吸着した2価の金属イオンの還元作用により、ガラス基板の表面に触媒核を形成させる。通常、0.05g/1程度の塩化パラジウム水溶液が好適に使用され、常温で塩化パラジウム水溶液が好適に使用され、常温で塩化パラジウム水溶液中に1~3分程度浸漬させる。

【0015】活性化工程で処理されたガラス基板は、60℃以上、かつ70℃未満の温度のNiP無電解メッキ浴に浸漬することによってNiP無電解メッキされる。NiPメッキ浴の温度が、60℃未満であると著しく製膜速度が遅くなるため工業的生産において望ましくない。また、70℃以上の高温であると感受性化処理時にガラス基板表面に吸着したPdが、メッキ浴に浸漬した際にメッキ液と反応し、激しく水素が発生する。そのため、この水素が、ガラス基板とメッキ膜の間に入り込み、NiPメッキ膜の密着性を低下させる。

【0016】すなわち、本発明者らの知見によれば、70℃未満の低温で無電解メッキを行うことにより、より強固な密着性を有するNiP膜ができる。NiP無電解メッキ浴は、通常、市販のものが使用され、ガラス基板はメッキ浴中で所定時間処理される。NiP無電解メッキ層の厚さは任意に選択されるが、良好な磁気記録媒体のためには、 $1\sim10\mu$ mの範囲が良い。

【0017】NiP無電解メッキを施したガラス基板は、必要に応じて研磨処理を行ったり、レーザービームによるテキスチャリング、機械テキスチャリング等のテキスチャー処理を適宜行うことができ、更には、常法に従って下地層、磁性層、保護層及び潤滑層等が積層される。本発明によれば、上記のようなガラス基板にNiP無電解メツキを行うことにより、ガラス基板とNiP無電解メツキ膜との剥離等を引き起こさない充分な強さの密着性を有し、耐衝撃性に優れた磁気記録媒体を得ることが可能となる。

[0018]

【実施例】以下、実施例により本発明を更に詳細に説明 するが、本発明はその要旨を越えない限り、以下の実施 例に限定されるものではない。

【0019】実施例1

市販の SiO_2-Li_2O 系の結晶化ガラスを使用し、固定砥粒による研削(グライディング)処理を行った後、研削剤(フジミインコーポレーティッド社製、商品

名「人造研削剤FO(複合人造エメリー)」: 比重3.90以上: Al_2O_345 重量%以上、TiO2.0重量%以下、ZrSiO49重量%以下: 粒度区分#1000(最大粒子径27 μ m以下)) によりラッピング処理を行った。

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【0020】その後、ガラス用アルカリ洗剤(株式会社パーカーコーポレーション社製、商品名「PK-LCG22」)により浴温50℃で10分間、洗浄処理し、次いで水洗後、酸性フッ化アンモニウム(関東化学株式会社製、 $NH_4F\cdot HF$ 、JIS番号K8817)50g/1中に、室温で<math>2分間、上記結晶化ガラスを浸漬してエッチング処理を行い、水洗を行った。得られたガラス基板表面をSEMで3万倍で観察したところ、凹部の最大長は、 3.8μ mであった。

【0021】次に、ガラス基板を、市販00.05g/ $1のSnCl_2$ 水溶液に室温で2分間浸漬し、水洗を行い、感受性化処理を行った。その後、市販<math>00.05g/ $1のPdCl_2$ 水溶液に室温で2分間浸漬し、水洗を行い活性化処理を行った。次いで、メッキ浴温<math>68℃・16時間でNiP無電解メッキで膜厚 15μ moNiP

層を成膜した。さらに、メッキ後に密着性を向上させるため、150℃で1時間のベーキング処理を行った。このようにして得られたNiP層とガラス基板の密着性を評価した結果、評価点数が10であり、良好な密着性を有することが確認された。なお、ガラス基板とNiP無電解メッキ層との密着性は、JISK54008.15の基盤目試験により評価した。評価点数10は良好な密着性を有することを示す。

【0022】実施例2~3

NiP無電解メッキのメッキ浴温をそれぞれ68 \mathbb{C} 、62 \mathbb{C} とした以外は実施例1と同様の方法で、ガラス基板にNiP無電解メッキ層を形成した。ガラス基板とNiP無電解メッキ層との密着性の評価点数はいずれも10であり、良好な密着性を有する。

【0023】比較例1

NiP無電解メッキのメッキ浴温を90℃とした以外は 実施例1と同様の方法で、ガラス基板にNiP無電解メ ッキ層を形成した。密着性の評価点数は5であり、充分 な密着性を得ることができなかった。

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(72)Inventor: SAIKI ATSUSHI

OKADA HIDEO

(54) PRODUCTION OF SUBSTRATE FOR MAGNETIC RECORDING MEDIUM

(57)Abstract:

PROBLEM TO BE SOLVED: To obtain a substrate having excellent adhesion property between a glass substrate and a NiP electroless plating layer and having high shock resistance and surface smoothness, and to stably obtain low floating height of a head by controlling the temp. of a NIP plating bath to a specified range in a NiP electroless plating process. SOLUTION: A glass substrate having fine recesses on the surface is used so as to obtain adhesion with a NiP electroless plating layer. The glass substrate is dipped in a NiP electroless plating bath at a temp. between $\geq 60^{\circ}$ C and $< 70^{\circ}$ C C for NiP electroless plating. If the bath temp. is $< 60^{\circ}$ C, the film forming rate significantly decreases, which is not desirable for industrial purpose. If the temp. is $\geq 70^{\circ}$ C, Pd adsorbed to the glass substrate in the treatment to add susceptibility reacts with the plating liquid to decrease the adhesion of the NiP plating film when the substrate is immersed in the plating bath. By this method, the obtd. magnetic recording medium has enough adhesion which does not cause peeling between the glass substrate and the NiP electroless plating film and the medium is excellent in shock resistance.

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SOLUTION: A glass substrate having fine recesses on the surface is used so as to obtain adhesion with a NiP electroless plating layer. The glass substrate is dipped in a NiP electroless plating bath at a temp. between ≥60° C and <70° C C for NiP electroless plating. If the bath temp. is <60° C, the film forming rate significantly decreases, which is not desirable for industrial purpose. If the temp. is ≥70° C, Pd adsorbed to the glass substrate in the treatment to add susceptibility reacts with the plating liquid to decrease the adhesion of the NiP plating film when the substrate is immersed in the plating bath. By this method, the obtd. magnetic recording medium has enough adhesion which does not cause peeling between the glass substrate and the NiP electroless plating film and the medium is excellent in shock resistance.

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CLAIMS

[Claim(s)]

[Claim 1] A manufacture method of a substrate for magnetic-recording data medium which is the manufacture method of a substrate for magnetic-recording data medium of coming to prepare a susceptibility-ized production process, an activation production process, and a NiP electroless deposition production process in a glass substrate one by one, and is characterized by temperature of a NiP plating bath in a NiP electroless deposition production process being 60 degrees C or more and less than 70 degrees C [claim 2] A manufacture method of a substrate for magnetic-recording data medium according to claim 1 that temperature of a NiP plating bath is characterized by being 65-69 degrees C [claim 3] A manufacture method of a substrate for magnetic-recording data medium according to claim 1 or 2 characterized by a glass substrate consisting of SiO2-Li2 O system glass ceramics

[Translation done.]

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DETAILED DESCRIPTION

[Detailed Description of the Invention]

[The technical field to which invention belongs] This invention relates to the manufacture method of the substrate for magnetic-recording data medium. Specifically, it is related with the manufacture method of the substrate in high recording density magnetic-recording data medium, such as a thin film magnetic-recording disk of the cover half used by the information industry etc. It is involved in the method of forming the high NiP electroless deposition layer of a glass substrate and adhesion especially.

[Description of the Prior Art] In recent years, many hard disk equipments are used as external storage of information processors, such as a computer. After the magnetic disk carried in this hard disk equipment generally forms a NiP electroless deposition layer in the surface of the nonmagnetic substrate which consists of an aluminium alloy and performs necessary data smoothing, texture ring processing, etc., on it, it carries out sequential formation of a nonmagnetic metal substrate layer, a magnetic layer, a protective layer, the lubricating layer, etc., and is produced. [0003] In the magnetic disk drive, although the arm head for record playback is moving by the fixed flying height in the magnetic-recording data-medium top, this flying height is very small in recent years with the rapid increment in the surface recording density of magnetic-recording data medium. Moreover, in order for the miniaturization of a magnetic disk drive and lightweight-ization to also progress quickly and to correspond to these, it is required to make still smaller granularity of the surface of magnetic-recording data medium, and data-medium surface roughness is already small to about several angstroms by Ra. Furthermore, since the shock resistance required of a magnetic disk since it corresponds to the hard disk equipment of a portable mold is also becoming 400G-800G, and a high value, in the substrate which consists of the conventional aluminium alloy to shock resistance, correspondence is difficult. Then, the glass substrate which can attain very small surface roughness and is excellent also in the mechanical strength instead of the aluminium alloy substrate from standpoints, such as shock resistance and surface smooth nature, is beginning to be used. [0004] In many cases, in the aluminium alloy substrate which performed NiP electroless deposition, the concentric circle-like texture ring is given to the substrate circumferencial direction by polishing on the surface. If this is good, it mainly closes the friction property between the arm head for record playback, and magnetic-recording data medium, and it aims at securing endurance. Moreover, in recent years, to replace with the texture ring by polishing and to form a projection only in a CSS zone with the texture ring by the laser beam, i.e., a laser beam, in connection with the flying height of the arm head at the time of magnetic disk drive actuation being remarkably small, is tried. (JP,8-129749,A

[0005] However, since the projection configuration controllability is bad, it is very difficult unlike the aluminium alloy substrate which performed NiP electroless deposition, to irradiate a direct laser beam and to form a projection in a glass plate. So, in order to apply laser texture technology to a glass substrate, it is necessary to form a NiP electroless deposition layer on a substrate beforehand.

[0006] The method of forming a NiP electroless deposition film on a glass substrate is proposed by JP,61-54018,A. However, it is technically difficult to form a NiP layer in a glass substrate with sufficient adhesion by the electroless deposition method. Then, in order to improve the adhesion of a glass substrate and a NiP electroless deposition film, the method of split-face-izing the glass substrate surface used for plating mechanically or chemically and the method of performing pretreatment of electroless deposition are proposed. for example, -- as the mechanical split-face-ized method -- aluminum 2O3 etc. -- the method which 100A or more of surface roughness grinds by center line average-of-roughness-height Ra with the grinding stone using an abrasive material is learned, and as the chemical ****-ized method, after carrying out alkaline degreasing, the method of etching by a hydrofluoric acid etc. is learned.

[0007] Moreover, as a method of pretreating electroless deposition, the solution of a stannous chloride performs a glass substrate, a palladium-chloride solution performs activation to JP,7-272263,A, JP,6-212440,A, etc. after sensitization, and the method of subsequently performing NiP electroless deposition for this glass substrate under an elevated temperature (70 degrees C or more or 80 degrees C or more) is proposed.

[Problem(s) to be Solved by the Invention] However, by these methods, the NiP layer which has sufficient adhesion and smooth nature to obtain a good magnetic disk was not able to be formed by the electroless deposition method on the glass substrate. This invention is made in view of an above-mentioned point, and the purpose is excellent in the adhesion of a glass substrate and a NiP electroless deposition layer, and it has high shock resistance and surface smooth nature, and is in moreover offering the manufacture method of the substrate for magnetic-recording data medium that the low surfacing height of an arm head is obtained by being stabilized.

[Means for Solving the Problem] this invention persons reach [that an outstanding NiP layer which satisfies many above-mentioned requirements is formed on a substrate, and] a header and this invention by controlling temperature of a NiP plating bath in a NiP electroless deposition production process, as a result of inquiring wholeheartedly in view of the above-mentioned actual condition. That is, a summary of this invention consists in a manufacture method of a substrate for magnetic-recording data medium which is the manufacture method of a substrate for magnetic-recording data medium of coming to prepare a susceptibility-ized production process, an activation production process, and a NiP electroless deposition production process in a glass substrate one by one, and is characterized by temperature of a NiP plating bath in a NiP electroless deposition production process being 60 degrees C or more and less than 70 degrees C. [0010] Hereafter, this invention is explained to details. Especially as a glass substrate of this invention, although not limited, glass ceramics, alumino silicate glass, etc. are used preferably, for example. Glass ceramics are desirable and SiO2-Li2 O system glass ceramics are suitable especially. It is suitable for a glass substrate to use for the substrate surface a glass substrate which has a detailed crevice in order to secure adhesion with a NiP electroless deposition layer. More specifically, 20 micrometers or less of 10 micrometers or less of detailed crevices 5micro or less are especially used for the maximum width of a crevice suitably preferably still more preferably. Since a NiP film is formed into this detailed hole when it has a detailed crevice on the board surface, this heightens a physical anchor effect and is considered to strengthen adhesion with a glass substrate and a NiP deposit by this.

[0011] A crevice where the surface of a glass substrate is detailed can be formed for example, in a glass-ceramics substrate by using an etching agent of fluoric acid systems, such as fluoric acid, a potassium fluoride, and ammonium fluoride, and performing chemical etching processing. Without spoiling surface smooth nature to some extent, since an amorphous field on the surface of a substrate can be alternatively etched for chemical etching if crystallization glass is used, since this can form a crevice appropriately, it is suitable. Magnitude of a crevice can be controlled by choosing suitably concentration of an etching reagent, processing temperature, the processing time, etc. Moreover, in a high degree-of-hardness aluminosilicate substrate, a crevice can be formed by processing it by loose grain or grinding processing.

[0012] According to this invention, a substrate for magnetic-recording data medium excellent in the adhesion of a glass substrate and a NiP electroless deposition layer can be obtained by performing a susceptibility-ized production process and an activation production process and performing NiP electroless deposition to a glass substrate under specific conditions continuously. And before a susceptibility-ized production process, a degreasing production process is usually established. Moreover, a rinsing production process is established between each production process, and ion exchange water or ultrapure water is suitably used as wash water.

[0013] A degreasing production process is a production process which washes the surface of a glass substrate, for example, a method of using ultrapure water, an alkali cleaner, an acid cleaning agent, a surfactant, etc. is mentioned. A susceptibility-ized production process and an activation production process are production processes which give catalytic activity required in order to make a glass substrate start NiP electroless deposition. That is, the glass surface needs to form a catalyst nucleus of noble metals, such as Au, Pt, Pd, and Ag, on the surface of glass, in order to start electroless deposition, since there is no catalytic activity.

[0014] Each above-mentioned production process is carried out as follows by well-known method. (Reference besides the adhesion of surface technical Vol.44 No.10, and 1993"glass and non-electrolyzed nickel plating", and Shin-ichi Hotta.)

A divalent metal ion which consists of Sn, Ti, Pd, Hg, etc. is made to adsorb first in a susceptibility-ized production process. Usually, a tin chloride aqueous solution of a 0.05 g/l degree is used suitably, and it is immersed about 1 to 3 minutes into a tin chloride aqueous solution in ordinary temperature. Next, a catalyst nucleus is made to form in an

included activation solution containing noble metals which serve as the aforementioned catalyst nucleus as an activation production process on the surface of a glass substrate according to a reduction operation of a divalent metal ion which was immersed and adsorbed the above-mentioned glass substrate. Usually, a palladium-chloride aqueous solution of a 0.05 g/l degree is used suitably, and you make it immersed about 1 to 3 minutes into a palladium-chloride aqueous solution in ordinary temperature.

[0015] NiP electroless deposition of the glass substrate processed at an activation production process is carried out by being immersed in temperature (60 degrees C or more and less than 70 degrees C) of a NiP electroless deposition bath. Since film production speed becomes slow remarkably with temperature of a NiP plating bath being less than 60 degrees C, in industrial production, it is not desirable. Moreover, when Pd which stuck that it was an elevated temperature 70 degrees C or more to the glass substrate surface at the time of susceptibility-ized processing is immersed in a plating bath, it reacts with plating liquid, and hydrogen occurs violently. Therefore, this hydrogen enters between a glass substrate and a plating film, and reduces the adhesion of a NiP plating film.

[0016] That is, according to this invention persons' knowledge, a NiP film which has firmer adhesion is made by performing electroless deposition at less than 70-degree C low temperature. As for a NiP electroless deposition bath, a commercial thing is usually used, and predetermined time processing of the glass substrate is carried out in a plating bath. Although thickness of a NiP electroless deposition layer is chosen as arbitration, for good magnetic-recording data medium, the range of 1-10 micrometers is good.

[0017] If needed, polishing processing can be performed, or a glass substrate which performed NiP electroless deposition can perform suitably texture processing of a texture ring by laser beam, a machine texture ring, etc., and the laminating of a substrate layer, a magnetic layer, a protective layer, the lubricating layer, etc. is further carried out according to a conventional method. According to this invention, by performing NiP electroless deposition to the above glass substrates, it has the adhesion of sufficient strength which does not cause exfoliation with a glass substrate and a NiP electroless deposition film etc., and it becomes possible to obtain magnetic-recording data medium excellent in shock resistance.

[0018]

[Example] Hereafter, although an example explains this invention to details further, this invention is not limited to the following examples, unless the summary is exceeded.

[0019] After using the crystallization glass of the SiO2-Li2 O system of example 1 marketing and performing grinding (gliding) processing by bonded abrasive, abrasives (the product made from FUJIMIINKOPORE, more than more than trade name "artificial abrasives F0 (compound artificial emery)":specific gravity 3.90:aluminum203 45 % of the weight, 2.0 or less % of the weight of TiO(s), less than [ZrSiO49 % of the weight]:grain-size partition #1000 (27 micrometers or less of diameters of grain of maximum size)) performed wrapping processing.

[0020] Then, washing processing was carried out for 10 minutes at 50 degrees C of bath temperature with the alkali detergent for glass (the Parker, Inc. make, trade name "PK-LCG22"), and it rinsed by immersing for 2 minutes and the above-mentioned crystallization glass at a room temperature, and subsequently after rinsing and to the inside of 50g [/l.] acid ammonium fluoride (the Kanto chemistry incorporated company make, NH4 F-HF, JIS number K8817), performing etching processing. When the obtained glass substrate surface was observed by SEM at 30,000 times, the maximum length of a crevice was 3.8 micrometers.

[0021] Next, it is a glass substrate SnCl2 of commercial 0.05 g/l It rinsed by having been immersed in the aqueous solution for 2 minutes at the room temperature, and susceptibility-ized processing was performed. Then, PdCl2 of commercial 0.05 g/l It rinsed by having been immersed in the aqueous solution for 2 minutes at the room temperature, and activation was performed. Subsequently, the NiP layer of 15 micrometers of thickness was formed by NiP electroless deposition in 68 degrees C of plating bath temperature, and 16 hours. Furthermore, in order to raise adhesion after plating, baking processing of 1 hour was performed at 150 degrees C. Thus, as a result of evaluating the adhesion of the obtained NiP layer and a glass substrate, evaluation mark are 10 and having good adhesion was checked. In addition, the cross cut adhesion test of JISK 54008.15 estimated the adhesion of a glass substrate and a NiP electroless deposition layer. It is shown that the evaluation mark 10 have good adhesion.

[0022] Except having made plating bath temperature of an example 2 - 3NiP electroless deposition into 68 degrees C and 62 degrees C, respectively, it is the same method as an example 1, and the NiP electroless deposition layer was formed in the glass substrate. Each evaluation mark of the adhesion of a glass substrate and a NiP electroless deposition layer are 10, and have good adhesion.

[0023] Except having made plating bath temperature of example of comparison 1NiP electroless deposition into 90 degrees C, it is the same method as an example 1, and the NiP electroless deposition layer was formed in the glass substrate. The evaluation mark of adhesion are 5 and were not able to acquire sufficient adhesion.